Consider a resistive-load inverter circuit with vop=5v, len = 20LeA/V2, VTO = 0.8V, RL = 200KM, and W/L = 2. Calculate the critical voltages (VOL, VOH, VIL, VIH) on the VTC and the find the noise margins of the circuit. when the ilp voltage is low ie. when the driver n-mos transister is unt-off, the OIP high voltage can be found as, VON=VDD=5V

In Resistive load inverter, the transconductance of The driver transistor is kn=kn (W/L) = 40 MA/N2 and hence,

kmRL =
$$8V^{-1}$$

The output low voltage Vol is calculated by

The output low voltage Vol is calculated by

 $Vol = VDD - VTO + \frac{1}{kn \cdot Rl} - \frac{1}{(VDD - VTO + \frac{1}{kn \cdot Rl})^2 - \frac{2VDD}{kn \cdot Rl}}{(5 - 0.8 + \frac{1}{8})^2 - \frac{2 \cdot 5}{8}}$
 $= 5 - 0.8 + \frac{1}{8} - \frac{1}{$

The ceidical voltage VIL is given by VIL= VTO+ In.RL = 0.8+ 1 = 0.925 V

Finally, The critical voltage VIH is given by,

VZH = VTO + $\sqrt{\frac{8}{3}} \frac{VDD}{lenge} - \frac{1}{lenge} = 0.8 + \sqrt{\frac{8}{3}} \frac{5}{8} - \frac{1}{8} = 1.97V$

Low noise margin NML = VIL-VOL = 0.93-0.15=0.78V High noise margin NMH = VOH - VIH = 5.0 - 1.97 = 3.03V

Consider the following investees design problem: VDD=5V, kn = 30 MAIV2 and V70 = IV, design a resistiveload inverter usuit with VoL=0.2V. specifically, determine the (WIL) ratio of the driver transistor, and the Value of the load resistor Re that active the required Volis 34 km.

3) The driver transistor is operating in the linear region when the output voltage is equal to Vol, and the ilp voltage is equal to Von=VDD VDD-VOL = len (WIL). [2. (VOH-VTO). VOL -VOL]

Assuming Vol=0.2V & using the given values for the power supply voltage, the driver threshold voltage and the deiver transconductionce kin, we obtain

the following equation,

e deiver
$$\frac{18405 (0.000)}{1000 \text{ lowing equation } 1}$$

$$\frac{5 - 0.20}{\text{RL}} = \frac{30 \times 10^{6}}{2} \cdot \frac{\text{W}}{\text{L}} \left[\left(2 \times 4 \times 0.20 \right) - \left(0.20 \right)^{2} \right]$$